os/legar/aD

## ABSTRACT OF THE DISCLOSURE

A method for determining data stored by a memory cell. The memory cell has a select gate coupled to a wordline, a first electrode coupled to a bitline, and a second electrode coupled to a conductor. The method comprises: floating the bitline; applying a first voltage to the wordline; applying a second voltage to the conductor such that the bitline is set to a third voltage that is equal to the first voltage minus a threshold voltage of the memory cell; and sensing the third voltage to determine the data stored by the memory cell.

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